

**Silicon Transistor for
40-Watt
Quasi-Complementary-Symmetry
Audio Amplifiers**

RCA1C09 is an n-p-n homotaxial-base silicon power transistor packaged in the JEDEC TO-220AB (VERSAWATT) case. Two of these devices, driven in the class-B mode by the RCA1A06 and RCA1A05 silicon n-p-n and p-n-p transistors, can be used as output devices in audio-amplifier applications.

The 40-watt amplifier shown in Figs. 1 and 5 uses two RCA1C09 transistors as output units in conjunction with seven TO-39 transistors, 11 diodes, and a 64-volt split power supply. The amplifier output is directly coupled to an 8-ohm speaker. This 40-watt amplifier features ruggedness and economy in the mid-power range.

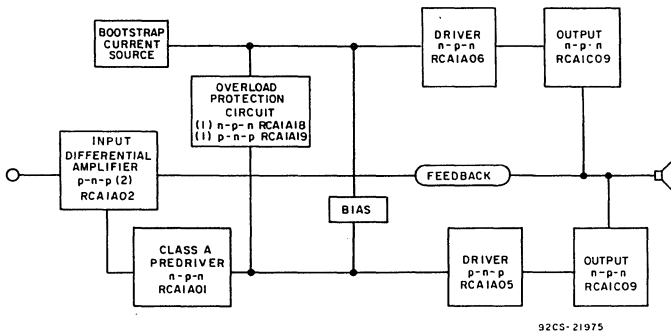


Fig.1— Block diagram and transistor complement for 40-watt quasi-complementary-symmetry audio amplifier.

MAXIMUM RATINGS, Absolute-Maximum Values:

COLLECTOR-TO-BASE VOLTAGE.....	V_{CBO}
COLLECTOR-TO-EMITTER VOLTAGE:	
With base open.....	V_{CEO}
With external base-to-emitter resistance (R_{BE}) = 100Ω.....	V_{CER}
EMITTER-TO-BASE VOLTAGE.....	V_{EBO}
COLLECTOR CURRENT.....	I_C
BASE CURRENT.....	I_B
TRANSISTOR DISSIPATION:	P_T
At case temperatures up to 25°C.....	
At case temperatures above 25°C.....	
TEMPERATURE RANGE:	
Storage & Operating (Junction).....	
PIN TEMPERATURE (During Soldering):	
At distances $\geq 1/32$ in. (0.8 mm) from case for 10 s max.....	

RCA1C09

V_{CBO}	75	V
V_{CEO}	65	V
V_{CER}	75	V
V_{EBO}	5	V
I_C	10	A
I_B	4	A
P_T		
	75	W
	See Fig. 2	
	-65 to 150	°C
	230	°C

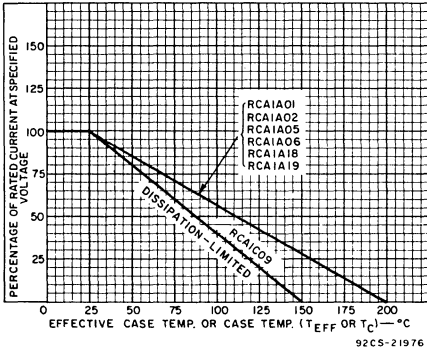


Fig. 2— Derating curves for all types.

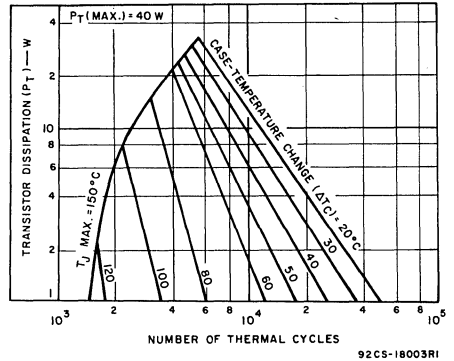


Fig. 3— Thermal-cycling ratings for RCA1C09.

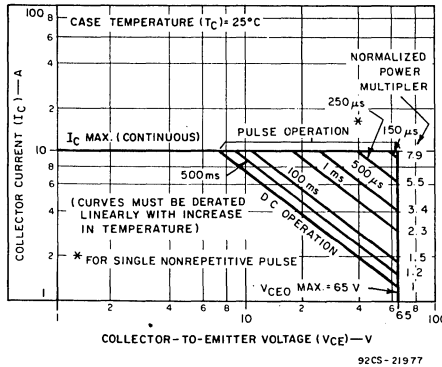
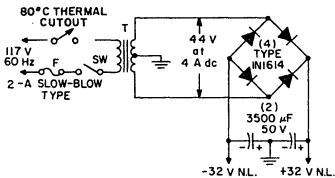
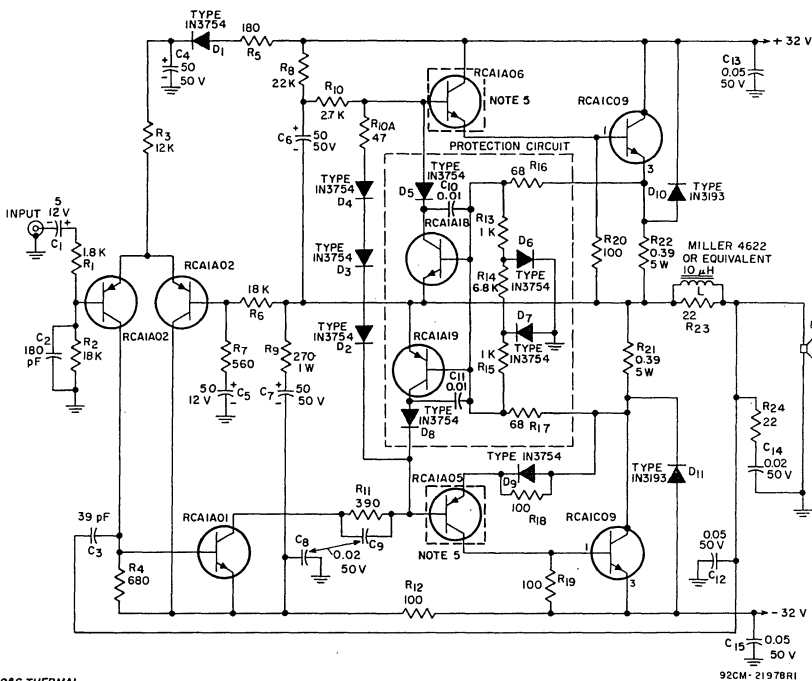


Fig. 4— Maximum operating areas for RCA1C09.



**TYPICAL PERFORMANCE DATA
For 40-Watt Audio Amplifier Circuit**

Measured at a line voltage of 120 V, $T_A = 25^{\circ}\text{C}$, and a frequency of 1 kHz, unless otherwise specified.

Power:

Rated power (8- Ω load, at rated distortion)	40 W
Typical power (4- Ω load)	55 W
Typical power (16- Ω load)	25 W
Music power (8- Ω load, at 5% THD with regulated supply)	55 W
Dynamic power (8- Ω load, at 1% THD with regulated supply)	50 W

Total Harmonic Distortion:

Rated distortion	1.0%
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IM Distortion:

10 dB below continuous power output at 60 Hz and 7 kHz (4:1)	0.1%
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Sensitivity:

At continuous power-output rating	600 mV
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Hum and Noise:

Below continuous power output:	
Input shorted	80 dB
With 2 k Ω resistance on 20-ft. cable on input	75 dB
Input Resistance	20 k Ω

NOTES:

1. T: Signal 88-2 (parallel secondary), Signal Transformer Co., 1 Junius St., Brooklyn, N.Y. 11212, or equivalent.
2. Resistors are 1/2-watt unless otherwise specified; values are in ohms.
3. Capacitances are in μF unless otherwise specified.
4. Non-inductive resistors.
5. Mount driver transistors on heat sink, Wakefield No. 209-AB, or equivalent. Alternatively, these types may be obtained with a factory-attached integral heat sink.
6. Provide approximately 1.3 $^{\circ}\text{C}/\text{W}$ heat sinking per output device.

Fig. 5—40-watt amplifier circuit featuring quasi-complementary-symmetry output.

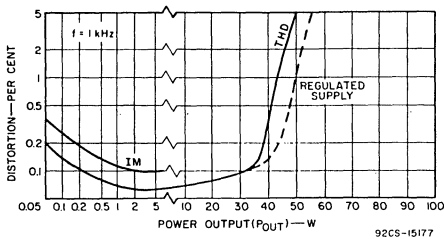


Fig.6— Distortion vs. power output.

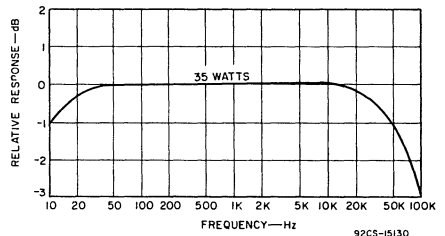


Fig.7— Response curve.

Type RCA1C09

Package: JEDEC TO-220AB

Construction: Silicon n-p-n, homotaxial base

ELECTRICAL CHARACTERISTICS, At Case Temperature (T_C) = 25°C Unless Otherwise Specified

CHARACTERISTIC	SYMBOL	TEST CONDITIONS	LIMITS		UNITS
			MIN.	MAX.	
Collector Cutoff Current: With external base-to-emitter resistance (R_{BE})	I_{CER}	$V_{CE} = 65 V, R_{BE} = 100\Omega$	—	1	mA
Emitter Cutoff Current: With collector open	I_{EBO}	$V_{EB} = 5 V, I_C = 0$	—	1	mA
Collector-to-Emitter Voltage: With external base-to-emitter resistance (R_{BE})	V_{CER}	$I_C = 0.2 A, R_{BE} = 100\Omega$	75	—	V
Gain Bandwidth Product	f_T	$I_C = 0.5 A, V_{CE} = 4 V$	0.8	—	MHz
DC Forward-Current Transfer Ratio	h_{FE}	$I_C = 4 A, V_{CE} = 4 V$	20	120	
Collector-to-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 4 A, I_B = 0.4 A$	—	1	V
Base-to-Emitter Voltage	V_{BE}	$I_C = 4 A, V_{CE} = 4 V$	—	1.5	V
Second-Breakdown Collector Current: With base forward biased	$I_{S/b}$	$V_{CE} = 40 V, t = 0.5 s$	1.87	—	A

For characteristics curves and test conditions, refer to published data for prototype 2N6103 (File 485).

TERMINAL CONNECTIONS FOR TYPE RCA1C09

- Lead 1 — Base
- Lead 2 — Collector
- Lead 3 — Emitter
- Lead 4 — Collector